

PMV52ENEAR Datasheet



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DiGi Electronics Part Number PMV52ENEAR-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PMV52ENEAR

Description MOSFET N-CH 30V 3.2A TO236AB

Detailed Description N-Channel 30 V 3.2A (Ta) 630mW (Ta), 5.7W (Tc) Su

rface Mount TO-236AB



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PMV52ENEAR	Nexperia USA Inc.
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	3.2A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	70mOhm @ 3.2A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
2.5V @ 250µA	3.3 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	100 pF @ 15 V
FET Feature:	Power Dissipation (Max):
	630mW (Ta), 5.7W (Tc)
Operating Temperature:	Grade:
-55°C ~ 175°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Supplier Device Package:	Package / Case:
TO-236AB	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
PMV52	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



PMV52ENEA 30 V, N-channel Trench MOSFET 7 May 2019

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic-level compatible
- Extended temperature range T_i = 175 °C
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 1 kV HBM (class H1C)
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- · Low-side load switch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	3.2	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 3.2 A; T_j = 25 °C		-	52	70	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	per Package					
	Name	Description	Version			
PMV52ENEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMV52ENEA	HQ%

[1] % = placeholder for manufacturing site code

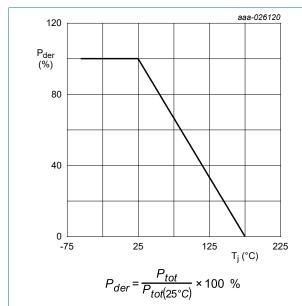
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	3.2	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	13	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	630	mW
			[1]	-	1.25	W
		T _{sp} = 25 °C		-	5.7	W
Tj	junction temperature			-55	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C
Source-drai	n diode			'	'	'
I _S	source current	T _{amb} = 25 °C	[1]	-	1.3	А
ESD maxim	um rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	1000	V
Avalanche r	uggedness		1	1		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.25 A; DUT in avalanche (unclamped)		-	3.8	mJ

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] [3] Measured between all pins.



Normalized total power dissipation as a Fig. 1. function of junction temperature

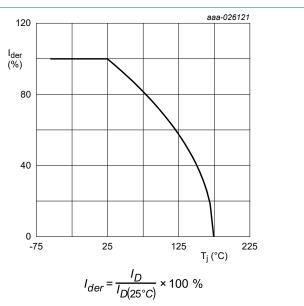


Fig. 2. Normalized continuous drain current as a function of junction temperature

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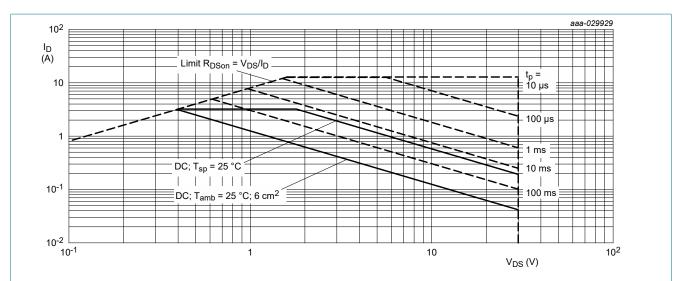


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	195	235	K/W
junction to ambient		[2]	-	100	120	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	18	26	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

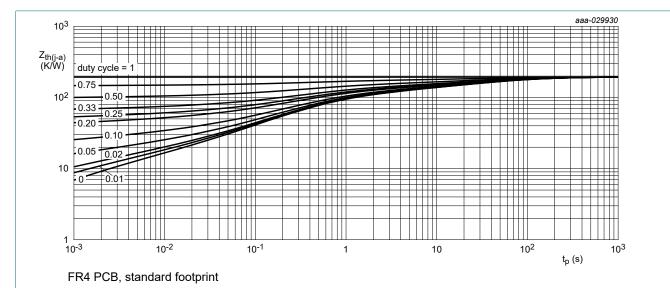


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

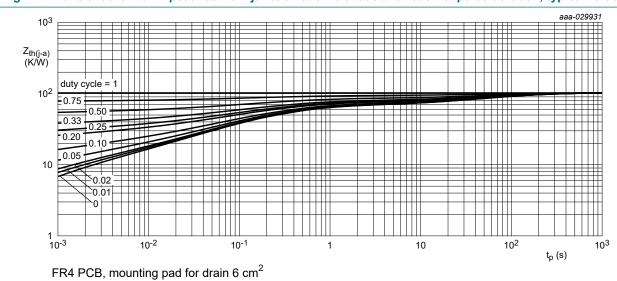


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1	1.5	2.5	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μΑ
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 3.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	52	70	mΩ
r	resistance	V _{GS} = 10 V; I _D = 3.2 A; T _j = 175 °C	-	93	124	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 2.7 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	70	100	mΩ
g _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 3.2 \text{ A}; T_j = 25 \text{ °C}$	-	5	-	S
R_G	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 3.2 A; V _{GS} = 10 V;	-	2.2	3.3	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.3	-	nC
Q_{GD}	gate-drain charge	1	-	0.6	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	100	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	30	-	pF
C _{rss}	reverse transfer capacitance		-	19	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 3.2 A; V _{GS} = 10 V;	-	2	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	13	-	ns
$t_{d(off)}$	turn-off delay time	1	-	6	-	ns
t _f	fall time	1	-	3	-	ns
Source-drai	in diode		,			
V _{SD}	source-drain voltage	I _S = 1.3 A; V _{GS} = 0 V; T _j = 25 °C	-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 1 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s; } V_{GS} = 0 \text{ V;}$	-	6	-	ns
Q _r	recovered charge	V _{DS} = 15 V; T _j = 25 °C	-	1	_	nC

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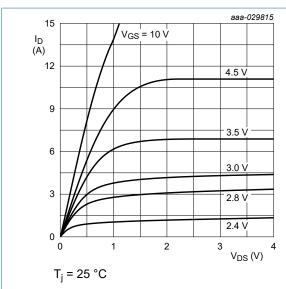


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

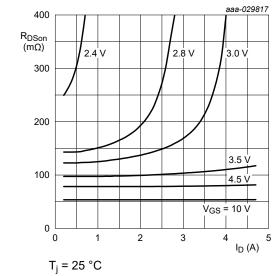


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

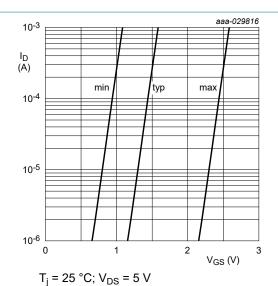


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

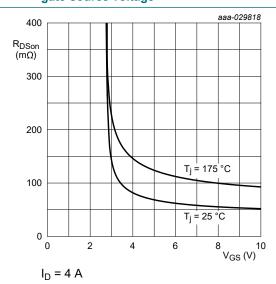


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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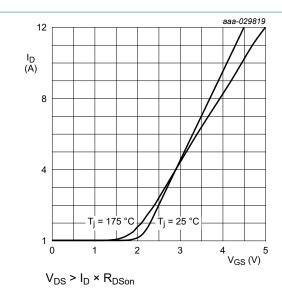


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

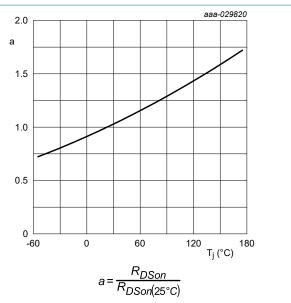


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

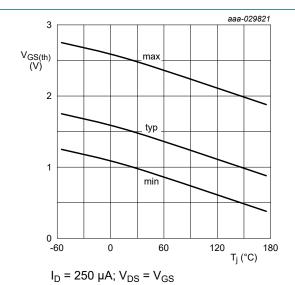


Fig. 12. Gate-source threshold voltage as a function of junction temperature

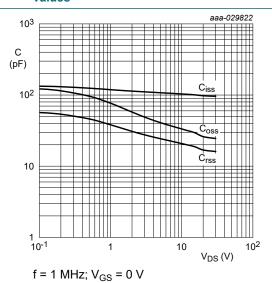


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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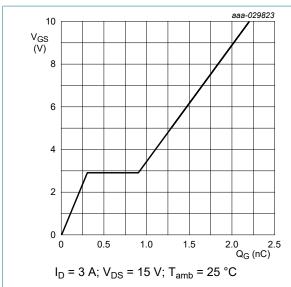


Fig. 14. Gate-source voltage as a function of gate charge; typical values

 $V_{GS} = 0 V$

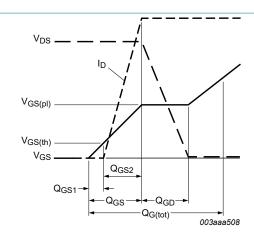


Fig. 15. Gate charge waveform definitions

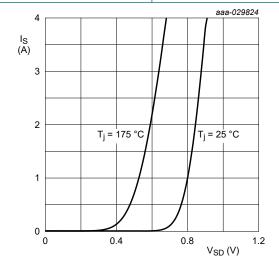
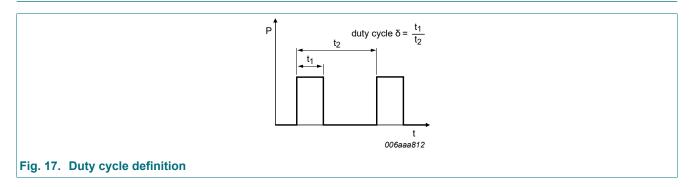


Fig. 16. Source current as a function of source-drain voltage; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

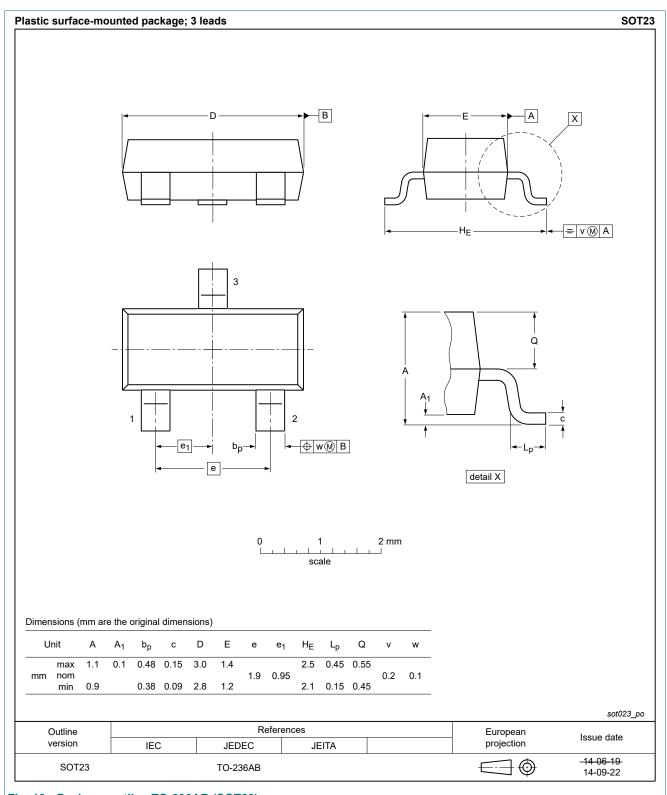
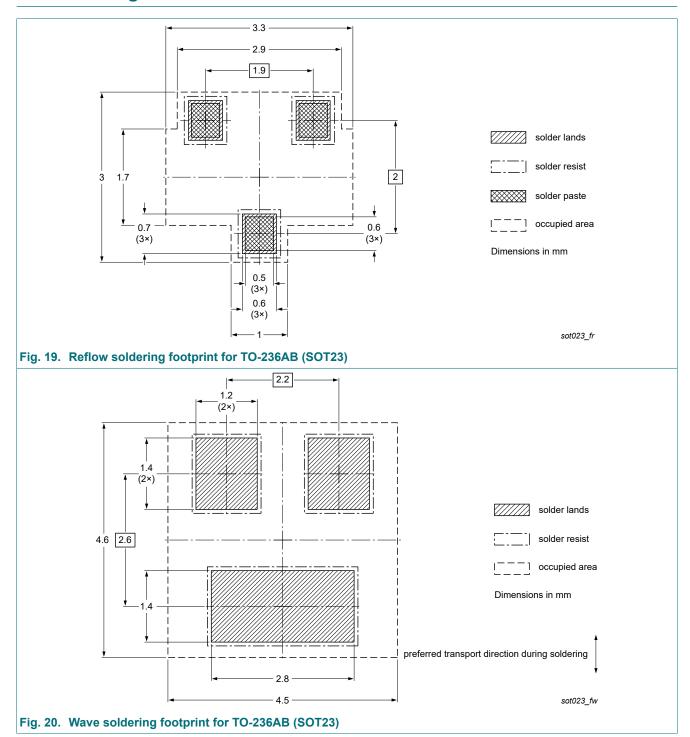


Fig. 18. Package outline TO-236AB (SOT23)

13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV52ENEA v.1	20190507	Product data sheet	-	-

PMV52ENEA

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 7 May 2019

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